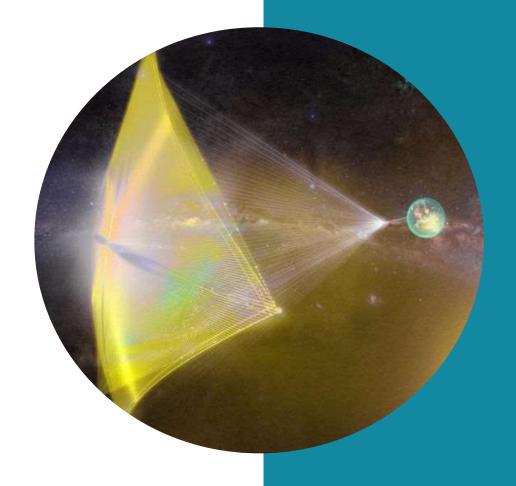


To achieve this, what's the challenge there?



New Material and Nano-technology



PART 4:
Signal, Data
storage/sorting



Power semiconductor devices



PART 5:

Power management

PART 3:

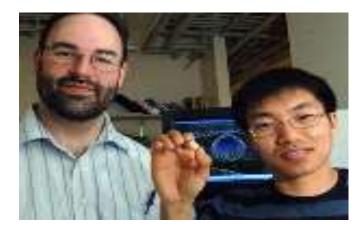
MEMS and Semiconductor Sensors

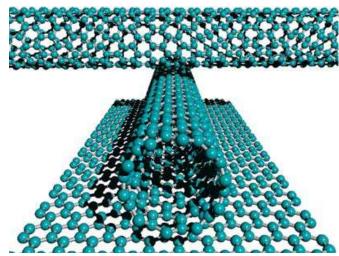


PART 6:
Opto-electronics

Nanoscale Materials & Devices

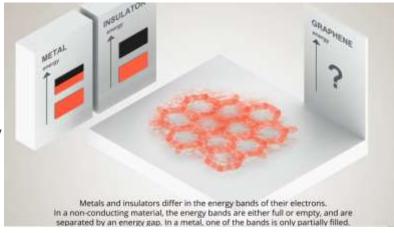
- Nanotechnology is science and engineering conducted at the nanoscale level
 - 1 to 100 nanometers
- Requires multiple disciplines:
 - Physics, material science, chemistry and measurement system design
- Nanoscale technologies have the potential to improve our quality of life
 - Medical delivery systems & detection
 - Faster electronics
 - Cheaper energy
 - Bio- and chemical detection systems





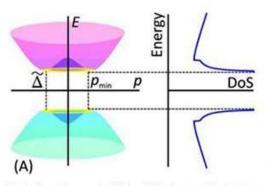
Nanoscale Materials & Devices

- Graphene:
 - 100 X stronger than the strongest steel
 - conducts heat and electricity efficiently
 - nearly transparent
 - And so on....



By Dexter Johnson Posted 19 May 2016 | 20:00 GMT





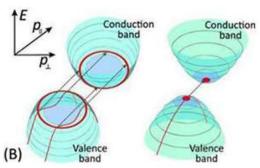


Illustration: Moscow Institute of Physics and Technology

Researchers at the Moscow Institute of Physics and Technology (MIPT) <u>new tunnel</u> <u>transistor based on bilayer</u> graphene

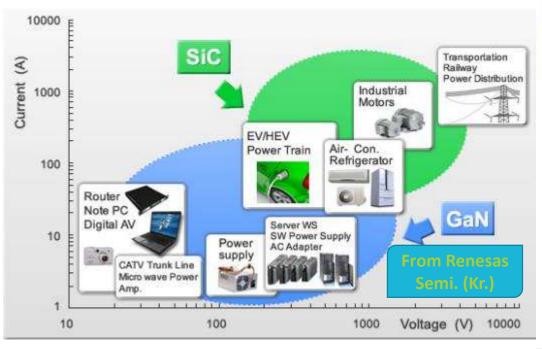
- reduce its power consumption
- increase in processors' clock speeds(two orders of magnitude)

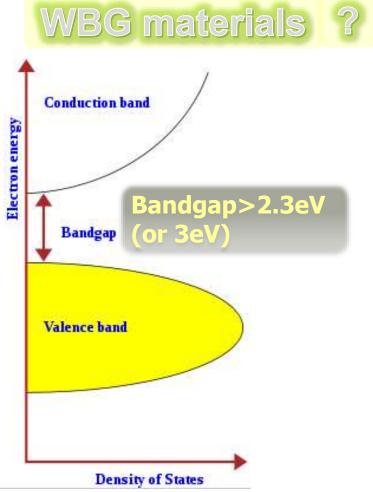
http://spectrum.ieee.org/nanoclast/semiconductors/materials/bilayer-graphene-could-usher-in-new-tunnél-transistor



Wideband Gap material: GaN, SiC

Wide bandgap materials are often utilized in applications in which high-temperature operation is important





WBG material: GaN, SiC

- Greater emphasis on commercialization of devices made from wide bandgap materials, especially SiC and GaN
 - Benefits of SiC and GaN:
 - Faster switching speed than Si → smaller passive components → smaller size and lower weight → higher efficiency
 - Lower switching losses than Si (especially lower recovery losses in diodes)
 - Lower leakage currents → better switch
 - Higher power density
 - Pack more power into smaller areas → higher efficiency
 - Higher operating temperature (especially SiC) → able to handle higher power with fewer parametric changes and without requiring cooling systems as extensive as silicon-based electronics → smaller size and higher efficiency









What is a Source Measure Unit (SMU)?

- Simultaneously source and measure voltage and/or current
- Perform resistance measurements



Precision DMM







Precision Power Supply



Electronic Load



True Current Source





Keithley SMU Family - Instruments



2400 SourceMeter SMU Instruments

- Family of single-channel models with I-V capability from 1100V to 100nV and 10.5A pulse to 1pA
- Smart alternative to separate Power Supplies and Digital Multimeters (DMMs)
- Convenient DMM-like user interface



2450 & 2460 Touchscreen SourceMeter SMU Instruments

Industry-first 5" color capacitive touchscreen GUI Test up to 200V and 1A (**2450**) or up to 100 V and 7A (**2460**) Sub pA and sub μ V resolution



2600B System SourceMeter SMU Instruments

- Family of dual- or single-channel models with I-V capability from 10A pulse to 0.1fA and 200V to 100nV
- TSP® (Test Script Processor) technology for best-in-class throughput and lowest cost of test
- Browser-based GUI enables testing on any PC from anywhere in the world



2650A Hi-Power System SourceMeter SMU Instruments

- Source and measure up to 3kV or 50A pulse, with best-in-class low current resolution
- Up to 2000W pulse or 200W DC power
- Optimized for characterizing and testing high power semiconductors, electronics, and materials



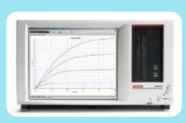


Keithley SMU Family - Systems



Parametric Curve Tracers

- Power device characterization up to 3kV and 100A including high quality instruments, cables, test fixturing, and software
- ACS Basic Edition software features real-time curve tracing and full parametric characterization modes
- Easily re-configurable to meet changing test needs



4200-SCS Semiconductor Parameter Analyzer

- An integrated analyzer for complete and precise characterization: I-V, C-V, Ultra-Fast I-V, and Pulse measurements
- Characterize devices, materials, and semiconductor processes with sub-fA resolution
- Easy-to-use Windows® GUI, modular architecture, and over 450 user-modifiable test applications simplify complex measurement



S530 Parametric Test Systems

- High-speed semiconductor parametric testing with low cost of ownership
- Designed for production and lab environments managing a broad range of devices and product wafers
- Proven SMU instrumentation technology ensures high measurement accuracy and repeatability



S500 Parametric Test Systems

- Highly configurable and scalable SMU instrument-based system
- Semiconductor device testing along with Automated Characterization Suite (ACS) at the device, wafer, or cassette level
- Ideal for SMU-per-pin Wafer Level Reliability (WLR) testing, high speed parallel test, die sort, and Process Control Monitoring (PCM)





New Material and Nano-technology



PART 4:
Signal, Data
storage/sorting

PART 2:

Power semiconductor devices



PART 5:

Power

management

PART 3:

MEMS and Semiconductor Sensors





PART 6:
Opto-electronics

Power semiconductor device:

- A power semiconductor device is a semiconductor device used as a switch or rectifier in power electronics; a switch-mode power supply is an example. Such a device is also called a power device or, when used in an integrated circuit, a power IC.
- Typical device : GTO / GTR / power MOSFET / IGBT







Characterization of power semiconductor device:

Characterization	Test Category	Devices and Parameters		
		IGBT	Power MOSFET	GTR
Static	ON-state	V _{CE-} I _C V _{GE-} I _C	$\begin{array}{c} V_{DS^{-}}I_{D} \\ VTH \\ V_{GS^{-}}I_{D} \\ R_{DS(on)} \end{array}$	V _{CE-} I _C Gummel plot
	OFF-state	I_{CEO} I_{CES} BV_{CES} BV_{CEO} BV_{CBS}	I _{GSS} I _{DSS} BV _{DSS} BV _{DG}	I _{CEO} I _{CES} BV _{CES} BV _{CEO}
Dynamic	Charge Capacitance	Q _G C _{iss} (a.k.a. C _{ies}) C _{oss} (a.k.a. C _{oes}) C _{rss} (a.k.a. C _{res})	Q _G C _{iss} (a.k.a. C _{ies}) C _{oss} (a.k.a. C _{oes}) C _{rss} (a.k.a. C _{res})	NA
Switching	Timing	$\begin{array}{c} T_{d(on)} \\ T_{r} \\ T_{d(off)} \\ T_{f} \end{array}$	$\begin{array}{c} T_{d(on)} \\ T_{r} \\ T_{d(off)} \\ T_{f} \end{array}$	T _s T _f

Static Characterization directly descripts DC performance and the quality of the devices, and the test is easy to perform.





Keithley Power Semi Test Solutions

MEET A WIDE RANGE OF CURRENT-VOLTAGE TESTING NEEDS

Up to 100A pulse for ON-State tests





Up to 3kV for OFF-State tests



Up to 10kV for breakdown voltage testing



Complete solution for ON-State, Off-State and C-V tests



NEW!! Up to 7A DC, 10A pulse for interactive ON-State testing

Keithley Power Semi Test Solutions

CONFIGURABLE SOLUTIONS

Single- or Dual-Channel SMU Instruments





COMPLETE SOLUTIONS

Parametric Curve Tracers



Options available:

- Software: ACS Basic Edition with built-in test libraries and real-time and parametric test modes
- Accessories: Test fixtures, protection modules, high voltage triaxial cables

A complete bench top system that includes a variety of SMU instruments, cables, test fixtures, and software for characterizing power devices





Power Semi Test Accessories

SUPPORT A VARIETY OF MEASUREMENT TYPES AND SIMPLIFY

SYSTEM INTEGRATION



Specialized Cabling









Test

High Power Test Fixtures





Overvoltage Protection Modules



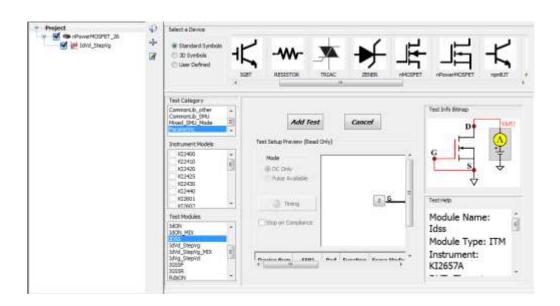


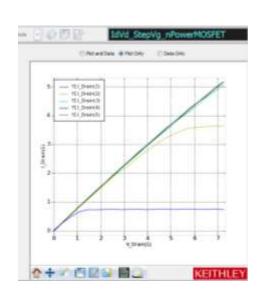
Power Semi Test Software

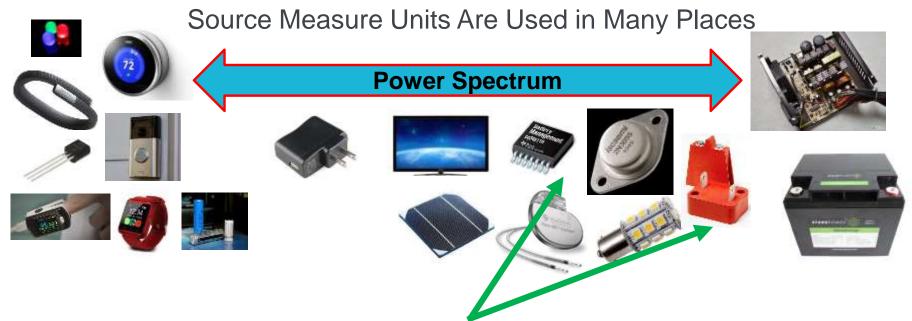
ACS BASIC, ACS



- ACS Software is the "glue" that brings all of the instruments together to make a solution
 - Supports Series 2400, 2600, and 4200 SMUs
- Includes hundreds of built-in device test libraries







For designers/researchers of lighting, power management, power conversion & control circuits and related devices

- Power transistor forward characteristics
- Battery Load Curves
- Charger simulation
- Dynamic load simulation
- 7A DC, 10A pulsed
- 2460/2461 SMU





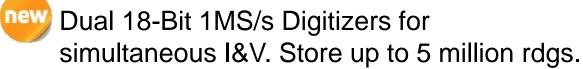


Model 2461 SourceMeter SMU

KEITHLEY CONTINUES TO INVEST IN ITS LINE OF GRAPHICAL SOURCE MEASURE UNITS

- 10A @ 100V 1000W Pulse version of the Model 2460
- 1000W Pulse Source/Sink, 100W DC Source/Sink
- Pulses as fast as 150μS. Dedicated pulse screen and commands







 Succeeds the Model 2430, 2420-C, 2425-C, 2430-C, 2440-C SourceMeter SMUs.
 Opportunity to upsell to the 2461.



IVy Android/iOS App – Visualize, Interact, Share For Series 2600B SourceMeter SMU Instruments



Visualize Instant Responses

 Swipe to change the source value and instantly see your device's response

Interact for Better Understanding

Pinch and zoom to gain deeper insight into your device's performance

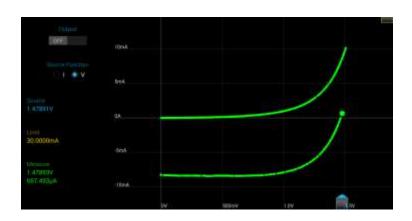
Share Your Results

Share screen shots and CSV files instantly using built-in Android tools

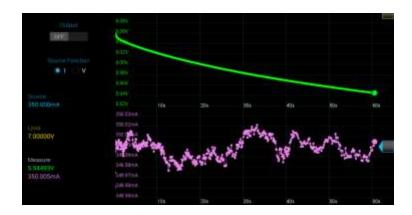




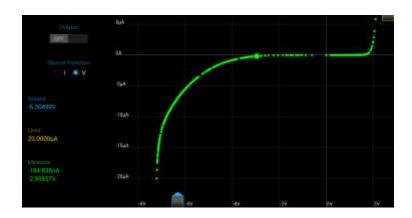
IVy Application Examples



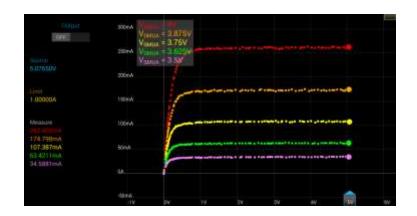
DUT comparison



LED Vf vs. Time



Diode Reverse Bias



MOSFET Family of Curves





PART 1: New Material and Nano-technology





PART 4: Signal, Data storage/sorting

PART 2: Power semiconductor devices





PART 5: Power management

PART 3: MEMS and **Semiconductor Sensors**



PART 6: Opto-electronics

MEMS Background





The technology of fabricating Micro mechanical structures (devices), Usually in Silicon wafers

Sensors: turn nonelectro-signal into electrical signal

Widely Used

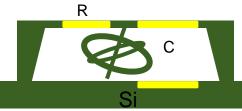
Stress

- Pressure/Force
- **♦** Light
- Vibration/ acoustic wave
- Fluidics
- Temperature

•••

Actuator: Micromotor moving or controlling a mechanism or system

Stress induced R, C...value change



Measurable electrical signal



Structures: delicate structures for special use (silicon pump, e.g.)

- Classical application:
 - Accelerometers, MEMS gyroscopes (used in Wii, smart phone...)
 - Silicon pressure sensors (car tire, blood pressure)
 - Bio-MEMS (biosensor, chemosensor)
 - Optical switching (for data communication)

0





MEMS (Micro-electromechanical Systems)

Keithley Solution for MEMS device test

- Customer application:
 - Test with sensor structure for its intrinsic characteristic without stress (pressure, vibration etc.)
 - To verify if fabricating process are within control.
 - Micro-phone:

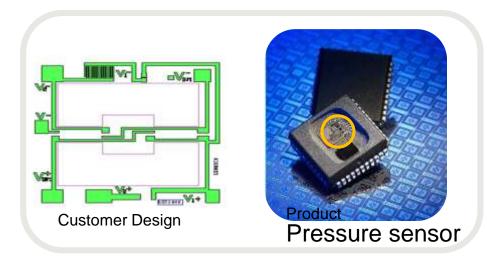
Voice → airflow → Capacitance change in MEMS sensor → electrical signal --- C test

Pressure sensor:

Pressure → R change in MEMS sensor → electrical signal --- R test

- Test requirement:
 - |-V:
 - R test: Force V measure I
 - V<10V</p>
 - R~ΚΩ
 - C-V:
 - Capacitance test
 - f=100KHz DCV<30V
 - C~10pF (0.1pF accu.)
 - wafer level with auto-prober





Keithley Test Solution:

• Configuration:

4200-SCS/C x 1ea4210-CVU*1

4200-SMU*2

4200-PA*1

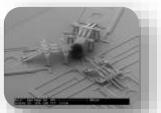
KEITHLEY **Ethernet Ethernet Hub** 4200-SCS/C- x 1ea Include 2*4200-SMU 4210-CVU 707B x 1ea 7174A x 1ea

707B x 1ea7174A x 1ea



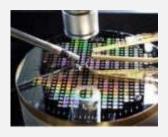


S500 system





Prober station



PART 1: New Material and Nano-technology





PART 4: Signal, Data storage/sorting

PART 2: Power semiconductor devices





PART 5: Power management

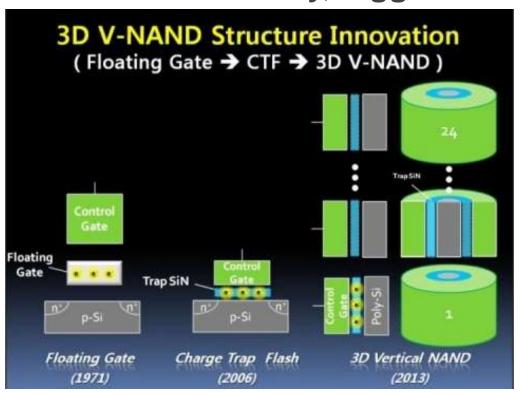
PART 3: MEMS and **Semiconductor Sensors**





PART 6: Opto-electronics

New Flash Memory, bigger and faster.

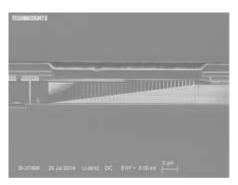


15.3TB SSD

מנעת.

ntel® SSD DC D3700 Series 800GB

3D Nand Flash tech. makes the massive data store more easier and faster.



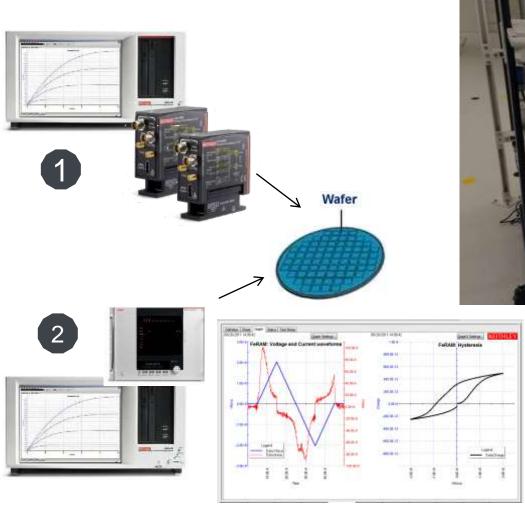
from

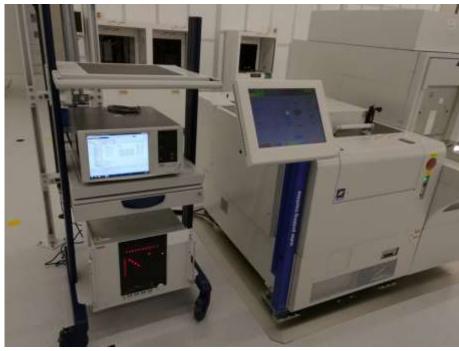
Samsung

From How Samsung connects to the wordlines in the array (courtesy Techinsights)



Non-volatile Memory Product Solutions

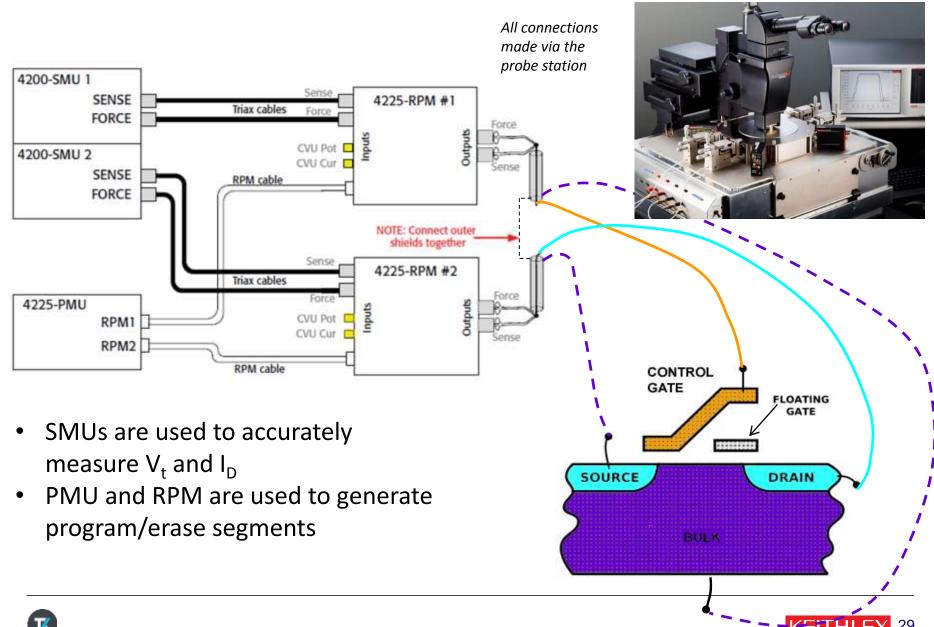




Configuration of Solution2 for 3D Nand Flash reliability test in one of our customer.



Example of Flash Memory Cell Test Setup



New Material and Nano-technology





PART 4:
Signal, Data
storage/sorting

PART 2: New power devices







PART 5: Power management

PART 3:

MEMS and Semiconductor Sensors





PART 6:
Optical energy and device

More power and wisely use them

- Increase the Capacity of battery
 - Ultra capacitor: Need of Public transportation
 - Electrochemistry research for new battery
- Decrease the power consumption.
 - More accurate Power measurement for different mode.

"The limitation to the number of sensors and amount of generated data is the battery life of the Wearable."

Battery capacity Power consumption control Measure Power Management...is crucial in wearable technology because poor ment power management translates into battery drain...Battery life has a direct impact on a product's real usefulness... Characterizing a usage profile is a nontrivial design activity. Mitch Maiman,

founder of Intelligent
Product Solutions

Credit Suisse





president and co-

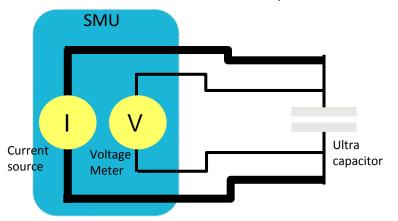
Using SMU for Ultra-capacitor test

- Test Instrument:
 - Keithley 2612/36B* for C<=20F
 - Keithley 2651A for C>=350F





- Connection:
 - 4-wires connection (remote sense)

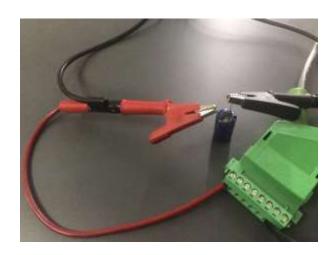


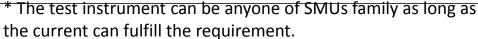
- Test Sample:
 - KAMCAP 10F Urate=2.7V
 - Maxwell 350F/3000F Urate=2.7V













Experiment – Result

for 10F capacitor with 2636B

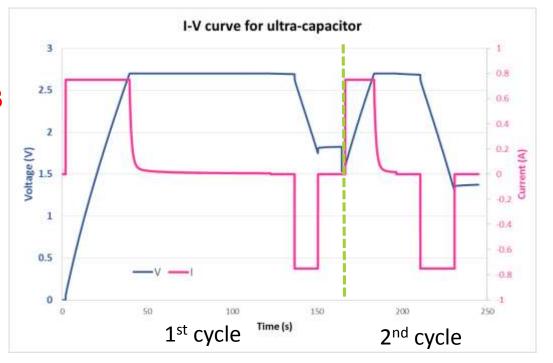
- Test result:
 - 2 cycles are tested

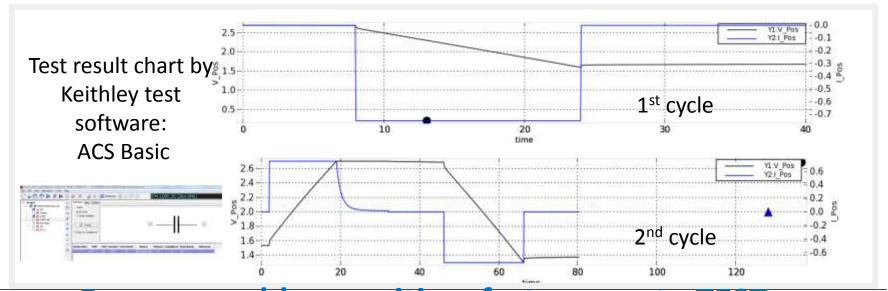
Cch =
$$I2 \times (t2 - t1) / (V2 - V1)$$

= 10.93 F

Cdch =
$$I5 \times (t5 - t4) / (V5 - V4)$$

= 10.88 F





Programmable, sensitive, fast, accurate TES

A Tektronix Company

Electrochemistry Applications



Basic Lab Research



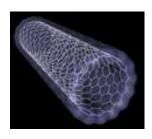
Electrode Development



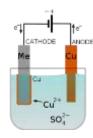
Electrolyte Research



Organic Semi



Nanomaterials



Electrodeposition



Dye-Sensitized Solar Cells



Health Care Sensors



Corrosion Resistance



Batteries



Fuel Cells



Supercapacitors

Electrochemistry is the cornerstone for many new products such as: batteries, glucose sensors, solar cells, coatings, medical devices etc.

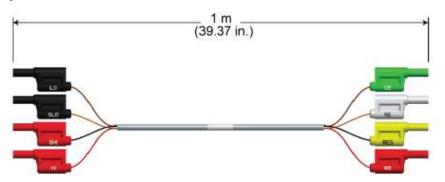
Involving Research, Design, Characterization, Performance Testing



Keithley's Electrochemistry test solution

- 2450-EC: 1A, 200V, 20W
 Potentiostat/Galvanostat
- 2460-EC: 7A, 100V, 100W
 Potentiostat/Galvanostat
- Includes:
 - Potentiostat (SMU)
 - Cable for 2,3 or 4 electrodes
 - Built-in software with test techniques
 - Full documentation







Keithley SMU for Electrochemistry Applications

GROWING LIBRARY OF TECHNIQUES

- Cyclic Voltammetry
- Linear Sweep Voltammetry
- Open Circuit Potential
- Potential Pulse and Square
 Wave with Current Measure
- Current Pulse and Square Wave with Voltage Measure
- Chronoamperometry
- Chronopotentiometry



Distinctive differences

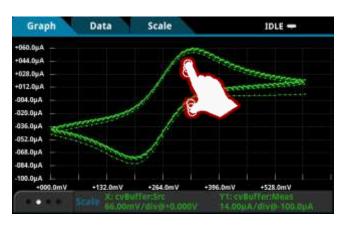
SIMPLICITY

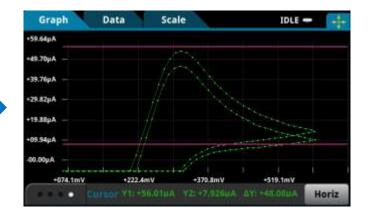
Simplify learning and test set-up

 Configure test, run experiment, generate voltammogram plot, analyze results

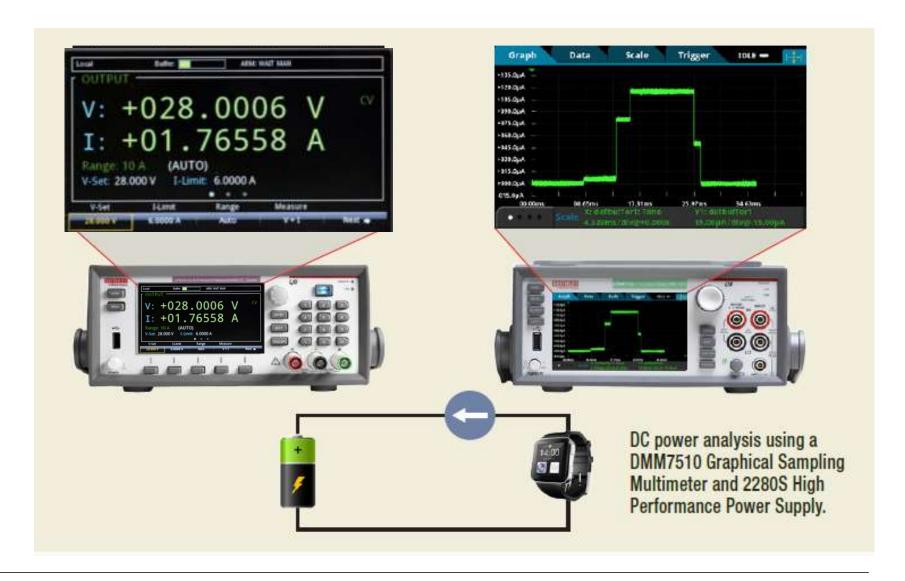








Solution for low power consumption measurement: DMM7510 + 2280S







Example Application

More Detailed Power Consumption Info with DMM7510







New Material and Nano-technology





PART 4:
Signal, Data
storage/sorting

PART 2:
Power
semiconductor
devices





PART 3:

MEMS and Semiconductor Sensors

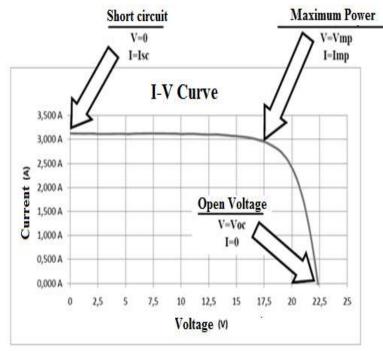




PART 6:
Opto-electronics

Optical energy: Solar cell









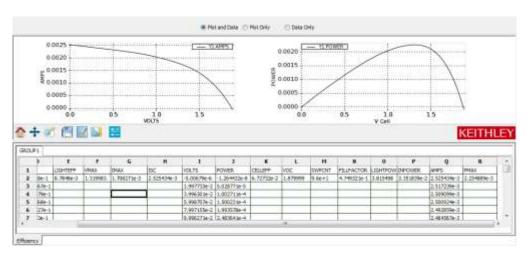
Keithley provides solution from single cell research test and mass production test.





Solar cell test solution:

 Based on SMUs' powerful capability of I-V characterization, solar cell test engineers are able to test the cell or cells more efficiently along with ACS Basic solar cell suit.



		Max.Cur.	Max.Volt.	Min.Cur/Volt.	Software
SolarCell-24	2450	±1.05A DC	±210V	10fA/10nV	ACS Basic
-51,60450 -7,60000A	2460	±7A DC	±100V	10fA/10nV	
SolarCell-26	2601B	±3A DC/ ±10A Pulse	±40V	100fA/100nV	ACS Basic
	2611B	±1.5A DC/ ±10A Pulse	±200V	100fA/100nV	
	2635B	±1.5A DC/ ±10A Pulse	±200V	10fA/10nV	
	2651A	±20A DC/ ±50A Pulse	±40V	0.1fA/100nV	

符号	参数名称		
Isc	短路电流		
Voc	开路电压		
Pmax	最大功率点		
Imax	最大功率点处的电流		
Vmax	最大功率点处的电压		
FF	填充因子		
η	转换效率		
Rsh	并联电阻		
Rs	串联电阻		

太阳能电池测试参数







Optical Module Components in Optical Communication

- Optical communication (a.k.a. optical telecommunication) is communication at a distance using light to carry information.
- Electrical signal (message) → optical signal
 → Electrical signal (information)



- Laser diode
- Photo detector



















Keithley solution for Optical Module Components test

Fiber

 Final DC test, Process control DC test, Coc parallel test, FA test for TOSA/ROSA, Tuneable, Coherent etc., telecom, Datacom products

PC (GPIB/LAN)

Optical Spectrum analyzer

Optical power meter

etc.

GPIB/LAN cable

Source CARE

DUT

2510

TEC

<u>Fixture</u>

26** SMU:

- 4-quadrant voltage/current source and measure instruments
- 10A pulse to 0.1fA and 200V to 100nV
- TSP (Test Script Processing) technology



6485/6487 Picoammeter/Source

- •10fA (10x10-15A) sensitivity
- •<200µV voltage burden
- •Bipolar 500V floating source
- Displays resistance

2602/2612/2636

Dual-C SMUs



Display: wearable, touchable,

Display

LCD: Liquid crystal display

TFT: Thing film Transistor

- liquid crystal molecular
- Backlight (light source)
- OLED: Organic Light Emitting Diode
 - "Sandwich" structure: organic semiconductor between two electrodes
 - Each pixel is LED/LEDs



LCD

OLED

a-Si

LTPS

AMOLED

IGZO

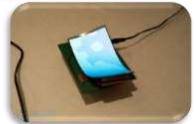
PMOLED

CGS











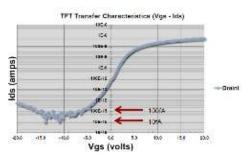




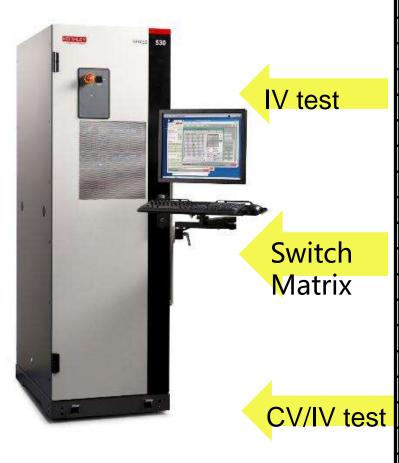


Keithley solution for Display

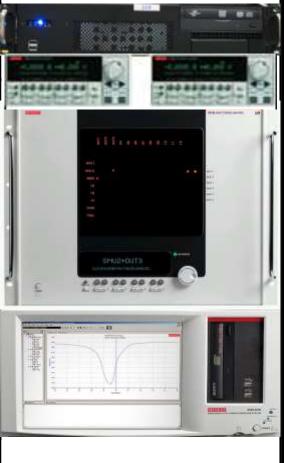








S500/S530:



S500/S530 system for TEG test in Display manufacture

PART 1: New Material and Nano-technology





PART 4: Signal, Data storage/sorting

PART 2: Power semiconductor devices







management

PART 3:

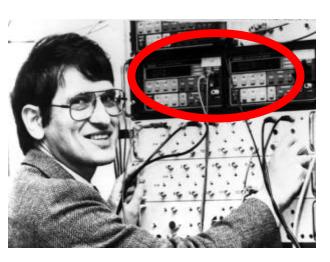
MEMS and **Semiconductor Sensors**





PART 6: Opto-electronics

Researchers use Our Sensitive Instruments to Make Great Scientific Discoveries



Dr. Klaus von Klitzing
1985 Nobel Prize in Physics
Quantized Hall effect



Dr. K. Alexander Muller and Dr. J. Georg Bednorz 1987 Nobel Prize in Physics Superconductivity in ceramic materials



Dr. Konstantin Novoselov 2010 Nobel Prize in Physics Graphene (two dimensional material)



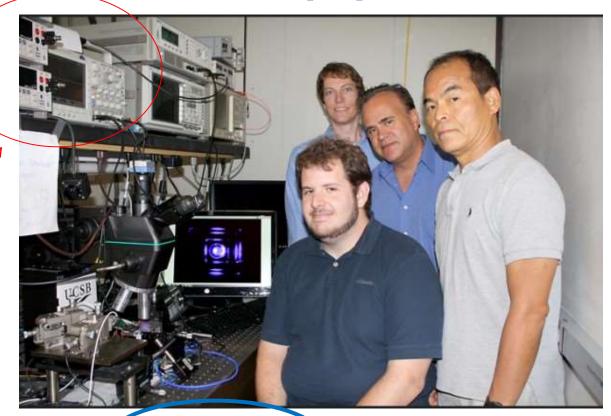


And They Need All Our of Equipment

Typical University/ Research Lab

- SourceMeters
- Scopes
- Power Supplies
- DMMs
- Other Equipment

2014 Physics Nobel Laureate for the development of the **Blue LED**



Shuji Nakamura) and his research group at UCSB.

Credit: UC Santa Barbara

Team that invented Violet Nonpolar **Vertical-Cavity Laser Technology**





Need More Sensitivity: The Most World's Most Sensitive Meter

Sensitivity:

0.000000000000001A (10⁻¹⁸A, 1aA)

= 6.241 electrons/second



Note: Q of $1e^{-} = 1.6X10^{-19}$ C $1A = 6.2 \times 10^{18}$ electron/second

Our Key Advantage:

The world's most sensitive current measurement instrument





Te//ronix®